NPN RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SRF 1136** is a Common Emitter Device Designed for class C Amplifier Applications up to 1 GHz.

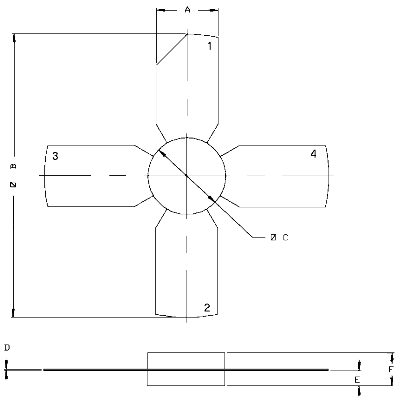
FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	800 mA
V_{CBO}	36 V
P_{DISS}	19 W @ T_C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	7.5 °C/W

PACKAGE STYLE 280 4L STUDLESS



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25,65	1.055/26,80
B	.220/5,59	.230/5,84
C	.270/6,86	.285/7,24
D	.003/0,08	.007/0,18
E	.117/2,97	.137/3,48
F	.5/2/14,53	
G	.130/3.30	
H	.275/6,99	.285/7,24
I	640/16,26	
J	.175/4,45	.21/75,51

1 = Collector 3 = Base
2 & 4 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 10 mA	36			**V**
BV_{CEO}	I_C = 20 mA	16			**V**
BV_{EBO}	I_E = 1 mA	3.0			**V**
h_{FE}	V_{CE} = 10 V I_C = 600 mA	25	100		**---**
C_{OB}	V_{CB} = 12.5 V f = 1.0 MHz		5		**pF**
$*P_G$					**dB**
$*\eta_C$					**%**

* RF SPECIFICATIONS ARE CONTROLLED BY CUSTOMER DRAWING AND ARE PROPRIETARY.